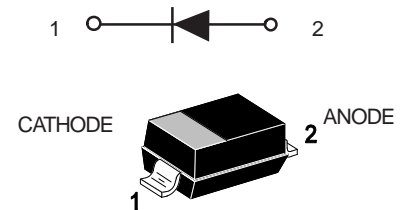


## HIGH VOLTAGE SWITCHING DIODE

### 1. FEATURES

We declare that the material of product compliance with RoHS requirements and Halogen Free.



SOD-123

### 2. DEVICE MARKING AND ORDERING INFORMATION

Marking: T3

### 3. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Continuous Reverse Voltage	VR	250	V
Peak Forward Current	IF	200	mA
Peak Forward Surge Current	IFM(surge)	625	mA
Non-Repetitive Peak Forward Current tp=10ms	IFSM	3.5	A

### 4. THERMAL CHARACTERISTICS

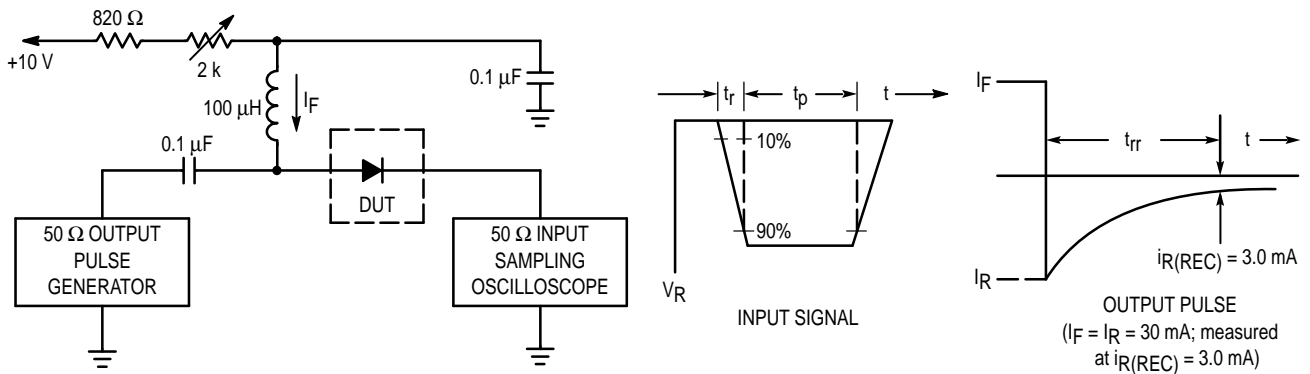
Parameter	Symbol	Limits	Unit
Total Device Dissipation FR-5 Board, (Note 1) TA = 25°C	PD	250	mW
Derate above 25°C		2	mW/°C
Thermal resistance from junction to ambient	RθJA	500	°C/W
Junction and Storage Temperature	TJ , Tstg	-55~+150	°C

1.FR-5 Minimum Pad

## HIGH VOLTAGE SWITCHING DIODE

### 5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Reverse Voltage Leakage Current (VR=200V)	IR	-	-	0.1	μA
(VR=200V, Tj=150°C)		-	-	100	
Reverse Breakdown Voltage (IBR=100μA)	VBR	250	-	-	V
Forward Voltage (IF=100mA)	VF	-	-	1.0	V
(IF=200mA)		-	-	1.25	
Diode Capacitance (VR =0V, f=1.0MHz)	CD	-	-	5	pF
Reverse Recovery Time (IF =IR =30mA, RL =100Ω)	trr	-	-	50	ns

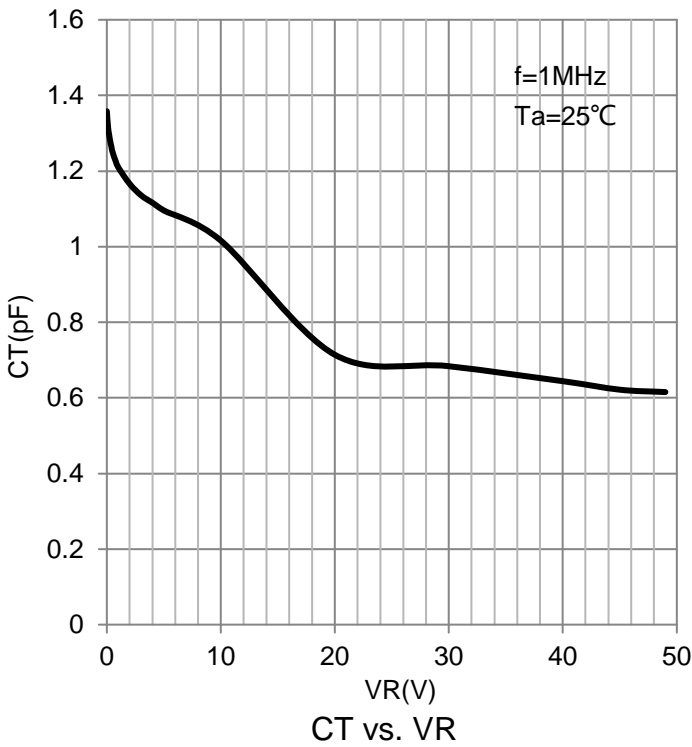
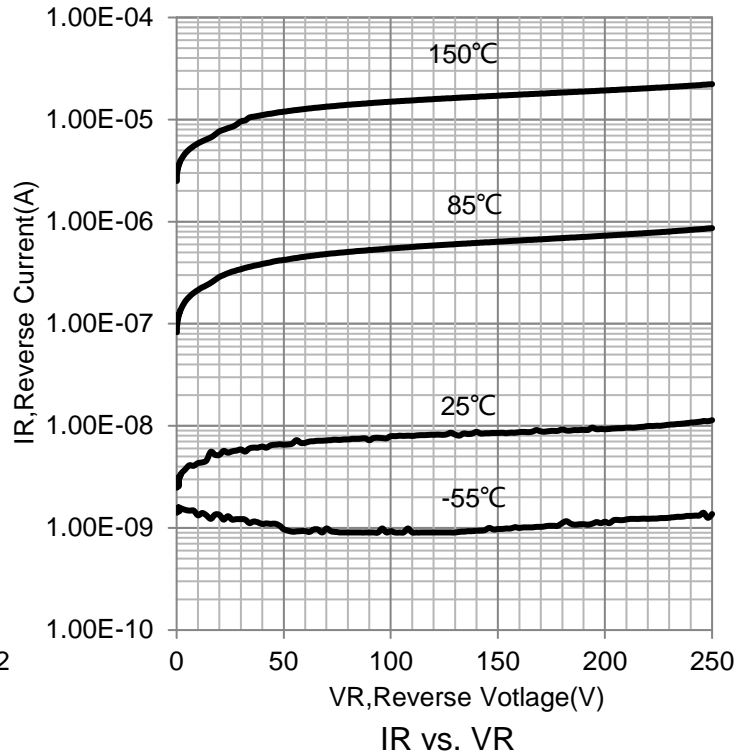
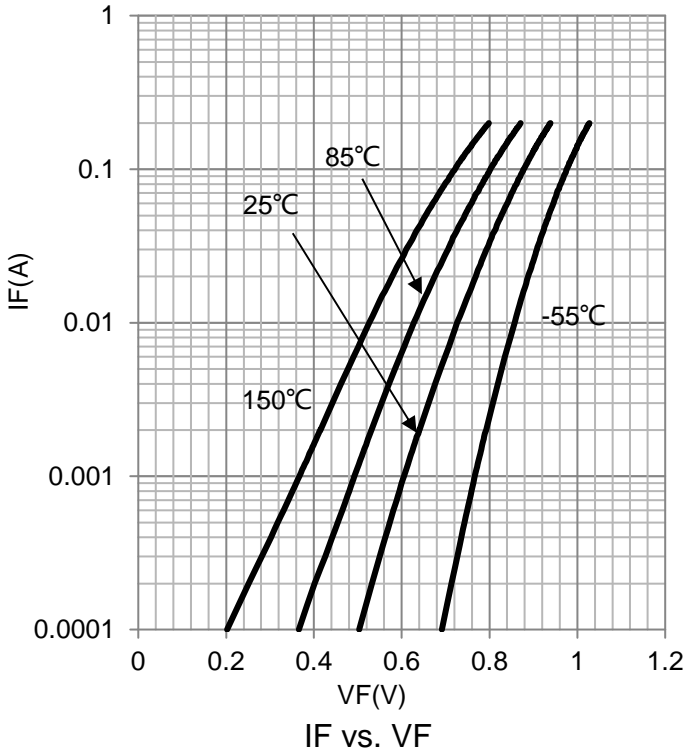


- Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current ( $I_F$ ) of 30 mA.  
 2. Input pulse is adjusted so  $I_{R(\text{peak})}$  is equal to 30 mA.  
 3.  $t_p \gg t_{rr}$

**Figure 1. Recovery Time Equivalent Test Circuit**

HIGH VOLTAGE SWITCHING DIODE

6.ELECTRICAL CHARACTERISTICS CURVES

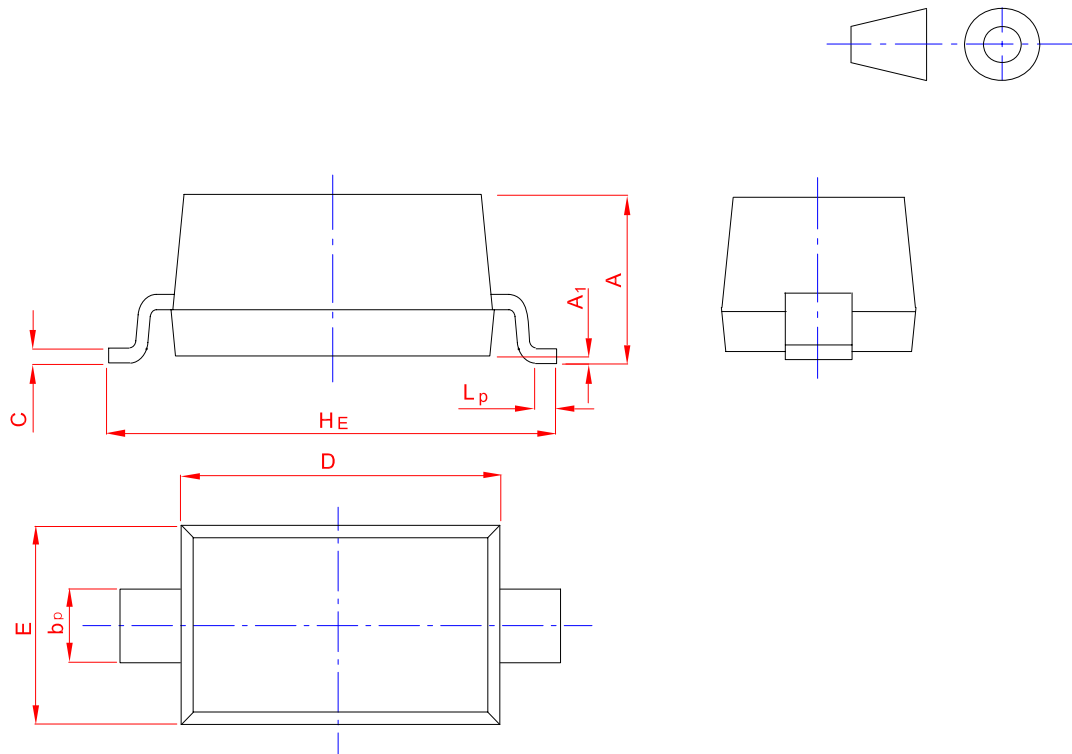


## HIGH VOLTAGE SWITCHING DIODE

### PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123



UNIT	A	b <sub>p</sub>	C	D	E	H <sub>E</sub>	A <sub>1</sub>	L <sub>p</sub>
mm	1.20	0.60	0.135	2.75	1.65	3.85	0.10	0.50
	0.90	0.50	0.100	2.55	1.55	3.55	0.01	0.20